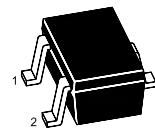
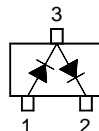


MMBD204SEW

SILICON EPITAXIAL PLANAR SWITCHING DIODE

Applications

- Ultra high speed switching



SOT-323 Plastic Package
Marking Code: **A7**

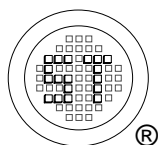
Absolute Maximum Ratings ($T_a = 25\text{ }^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Repetitive Peak Reverse Voltage	V_{RM}	20	V
Reverse Voltage	V_R	20	V
Average Rectified Forward Current	I_O	100	mA
Maximum (Peak) Forward Current (Single)	I_{FM}	200	mA
Peak Forward Surge Current ($t_p = 1\text{ }\mu\text{s}$)	I_{FSM}	300	mA
Power Dissipation	P_d	200	mW
Junction Temperature	T_J	150	$^\circ\text{C}$
Storage Temperature Range	T_s	- 55 to + 150	$^\circ\text{C}$

Characteristics at $T_a = 25\text{ }^\circ\text{C}$

Parameter	Symbol	Max.	Unit
Forward Voltage at $I_F = 10\text{ mA}$	V_F	1	V
Reverse Current at $V_R = 15\text{ V}$	I_R	0.1	μA
Capacitance between Terminals at $V_R = 6\text{ V}$, $f = 1\text{ MHz}$	C_T	4	pF

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SEMTECH ELECTRONICS LTD.

(Subsidiary of Sino-Tech International Holdings Limited, a company
listed on the Hong Kong Stock Exchange, Stock Code: 724)



ISO/TS 16949 : 2002
Certificate No. 05103



ISO 14001:2004
Certificate No. 7116

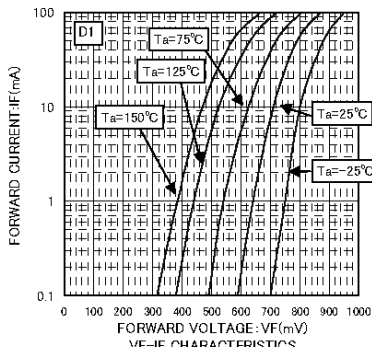


ISO 9001:2000
Certificate No. 0506086

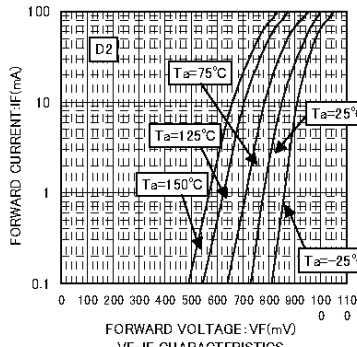
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Dated : 10/10/2008

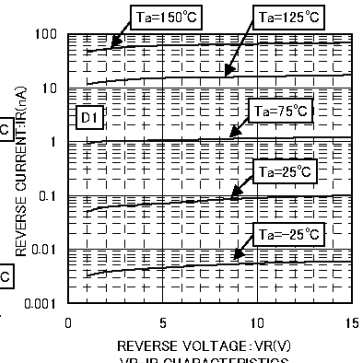
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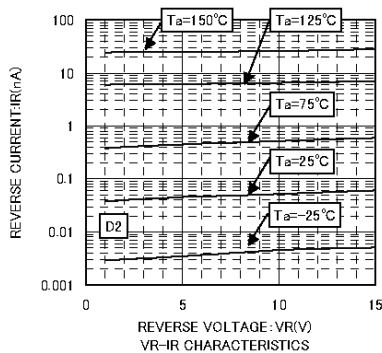
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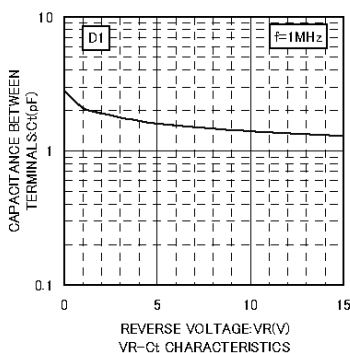
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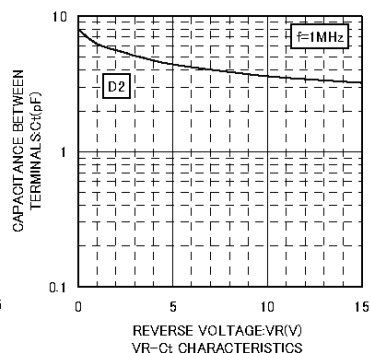
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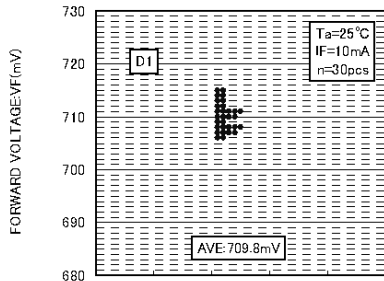
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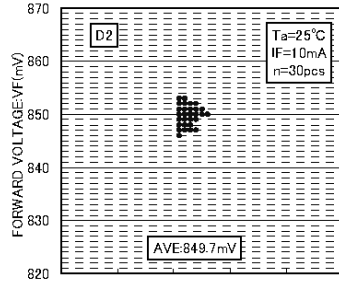
VR-Ct CHARACTERISTICS



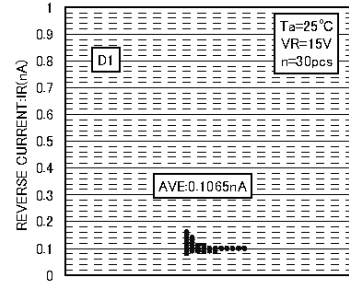
VR-Ct CHARACTERISTICS



VF DISPERSION MAP



VF DISPERSION MAP



IR DISPERSION MAP

